

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,806,095 B2
APPLICATION NO. : 10/092795
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INVENTOR(S) : Nallan et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the Title page, in field (56), under "Foreign Patent Documents", in column 2, line1, after "12/2001" insert -- H01L --.

In column 1, line 46, delete "HfO2, ZrO2" and insert -- HfO₂, ZrO₂ --, therefor.

In column 1, line 47, delete "HfSiO₂" and insert -- HfSiO₂--, therefor.

In column 1, line 53, delete "CL₂/CO" and insert -- Cl₂/CO --, therefor.

In columns 3-4, lines 66-67 and 1-2, below "The foregoing steps of the.....dielectric layer." delete "The foregoing steps of the.....dielectric layer."

(Repeated occurrence)

In column 4, line 40, delete "3500° C" and insert -- 350° C--, therefor.

In column 4, line 64, delete "hafniumoxide" and insert -- hafnium-oxide --, therefor.

In column 6, line 10, in Claim 11, delete "A" before "The".

In column 6, line 16, in Claim 12, after "material" insert -- , --.

In column 6, line 39, in Claim 17, after "gas;" insert -- and --.

Signed and Sealed this

Twenty-sixth Day of December, 2006



JON W. DUDAS

Director of the United States Patent and Trademark Office